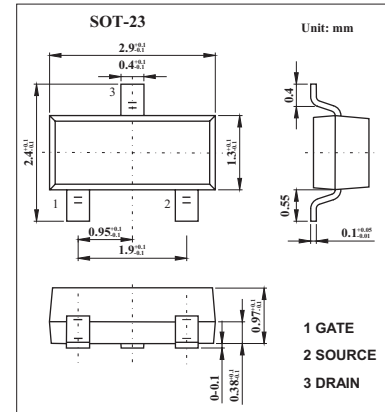
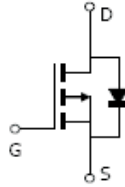


## P-Channel 20V (DS) MOSFET

## KI2321DS

## ■ Features

- $V_{DS}$  (V) = -30V
- $I_D$  = -4.2 A ( $V_{GS}$  = -10V)
- $R_{DS(ON)}$  < 50m $\Omega$  ( $V_{GS}$  = -10V)
- $R_{DS(ON)}$  < 65m $\Omega$  ( $V_{GS}$  = -4.5V)
- $R_{DS(ON)}$  < 120m $\Omega$  ( $V_{GS}$  = -2.5V)

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	$T_A=25^\circ\text{C}$	A
		$T_A=70^\circ\text{C}$	
Pulsed Drain Current	$I_{DM}$	-30	
Power Dissipation	$P_D$	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

## ■ Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Maximum Junction-to-Ambient*1	$R_{\theta JA}$	65	90	$^\circ\text{C/W}$
Maximum Junction-to-Ambient *1				
Maximum Junction-to-Lead *2	$R_{\theta JL}$	43	60	$^\circ\text{C/W}$

\*1 The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz.

Copper, in a still air environment with  $T_A = 25^\circ\text{C}$

\*2 . The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

## KI2321DS

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =250 μ A, V <sub>GS</sub> =0V	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V			-1	μ A
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C			-5	
Gate-Body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250 μ A	-0.7	-1	-1.3	V
Static Drain-Source On-Resistance	r <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.2A		42	50	m Ω
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A		53	65	m Ω
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1A		80	120	m Ω
On state drain current	I <sub>D(ON)</sub>	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-5V	-25			A
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-5A	7	11		S
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz		954		pF
Output Capacitance	C <sub>oss</sub>			115		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			77		pF
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		6		Ω
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-4A		9.4		nC
Gate Source Charge	Q <sub>gs</sub>			2		nC
Gate Drain Charge	Q <sub>gd</sub>			3		nC
Turn-On DelayTime	t <sub>D(on)</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>L</sub> =3.6 Ω, R <sub>GEN</sub> =6 Ω		6.3		ns
Turn-On Rise Time	t <sub>r</sub>			3.2		ns
Turn-Off DelayTime	t <sub>D(off)</sub>			38.2		ns
Turn-Off Fall Time	t <sub>f</sub>			12		ns
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =-4A, di/dt=100A/ μ s		20.2		ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =-4A, di/dt=100A/ μ s		11.2		nC
Maximum Body-Diode Continuous Current	I <sub>S</sub>				-2.2	A
Pulsed Body-Diode Current *	I <sub>SM</sub>				-30	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.75	-1	V

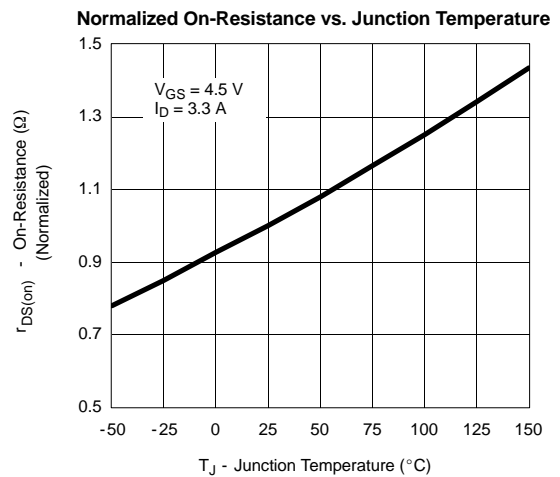
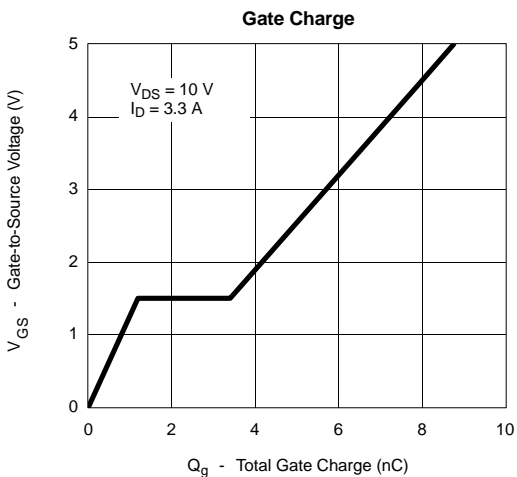
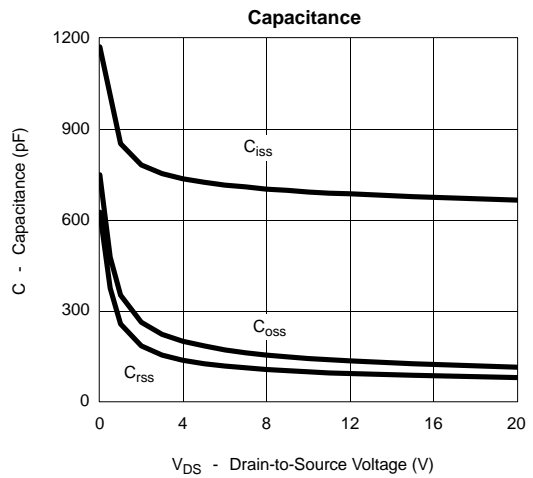
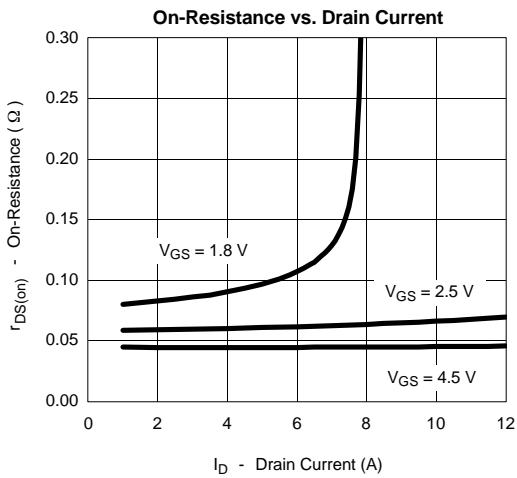
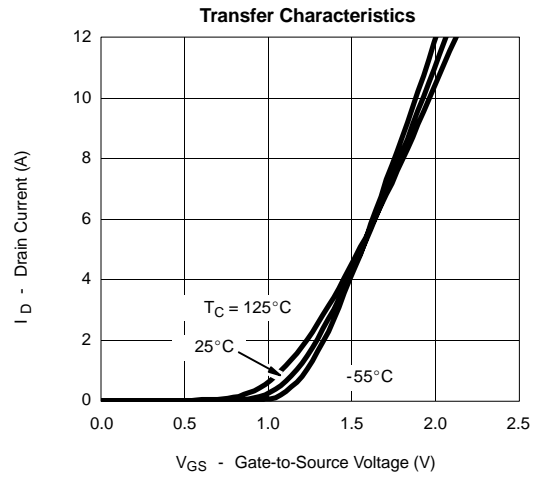
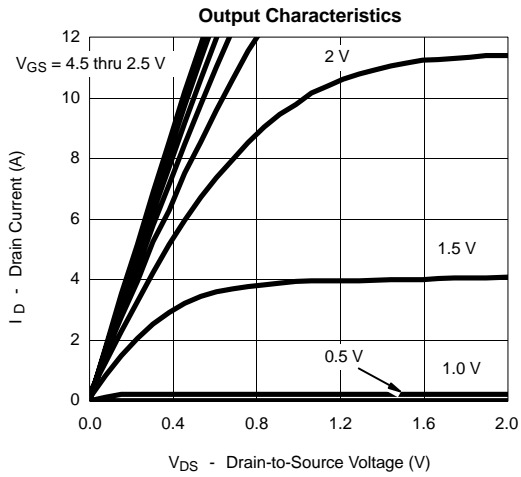
\* Repetitive rating, pulse width limited by junction temperature.

## ■ Marking

Marking	D1SUB
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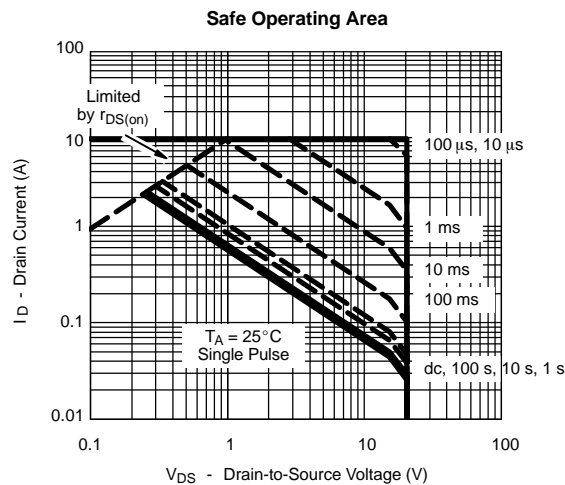
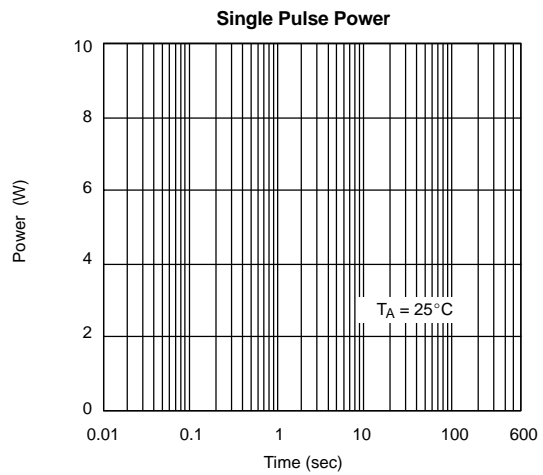
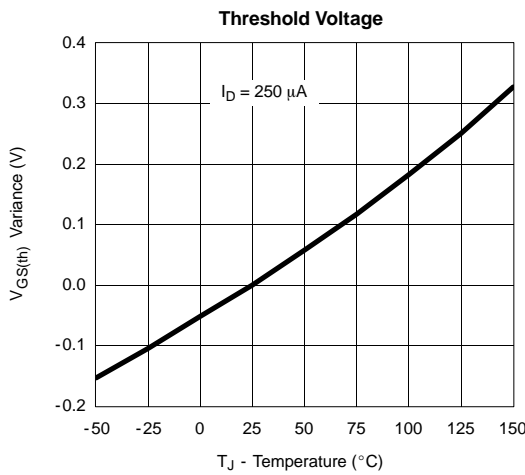
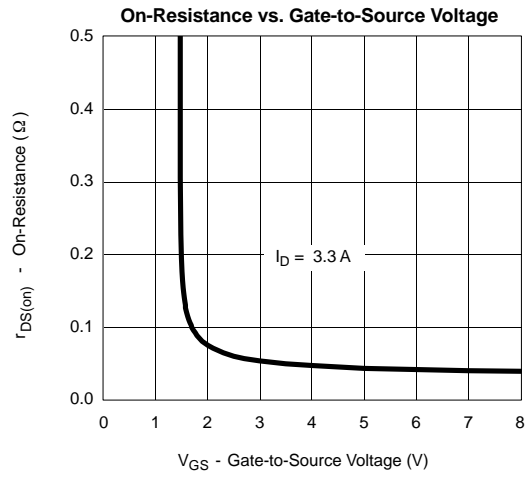
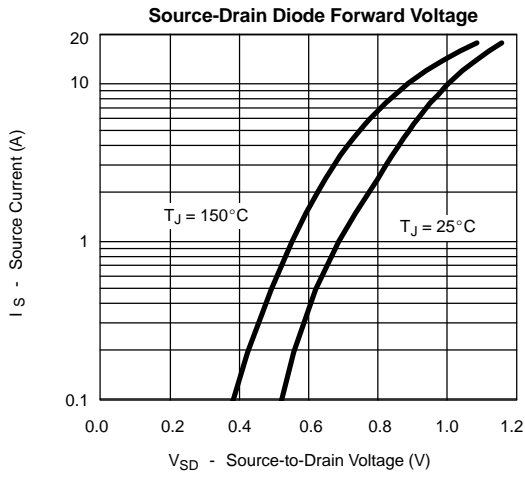
# KI2321DS

## Typical Characteristics



# KI2321DS

■ Typical Characteristics



## KI2321DS

## ■ Typical Characteristics

